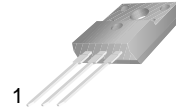


NPN Silicon Transistor

FJPF5027



1. Base
2. Collector
3. Emitter

TO-220 Fullpack, 3-Lead
CASE 221AT

High Voltage and High Reliability

- High Speed Switching
- Wide SOA
- This is a Pb-Free Device

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	1100	V
V _{CEO}	Collector-Emitter Voltage	800	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	3	A
I _{CP}	Collector Current (Pulse)	10	A
I _B	Base Current	1.5	A
P _C	Collector Dissipation (T _C = 25°C)	40	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55~150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

h_{FE} CLASSIFICATION

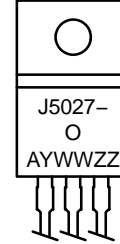
Classification	N	R	O
h _{FE1}	10~20	15~30	20~40

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1 mA, I _E = 0	1100	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 5 mA, I _B = 0	800	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1 mA, I _C = 0	7	-	-	V
V _{CEX(sus)}	Collector-Emitter Sustaining Voltage	I _C = 1.5 A, I _{B1} = -I _{B2} = 0.3 A L = 2 mH, Clamped	800	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} = 800 V, I _E = 0	-	-	10	μA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5 V, I _C = 0	-	-	10	μA
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} = 5 V, I _C = 0.2 A V _{CE} = 5 V, I _C = 1 A	10 8	- -	40 -	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.5 A, I _B = 0.3 A	-	-	2	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.5 A, I _B = 0.3 A	-	-	1.5	V
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	60	-	pF
f _T	Current Gain Bandwidth Product	V _{CE} = 10 V, I _C = 0.2 A	-	15	-	MHz
t _{ON}	Turn On Time	V _{CC} = 400 V, I _C = 5 I _{B1} = -2.5 I _{B2} = 2 A, R _L = 200 Ω	-	-	0.5	μs
t _{STG}	Storage Time		-	-	3	μs
t _F	Fall Time		-	-	0.3	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MARKING DIAGRAM



- J5027- = Specific Device Code
 O = h_{FE} Grade
 A = Site Code
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

ORDERING INFORMATION

Device	Package	Shipping [†]
FJPF5027OTU	TO-220 Fullpack	1000 Units / Tube

TYPICAL CHARACTERISTICS

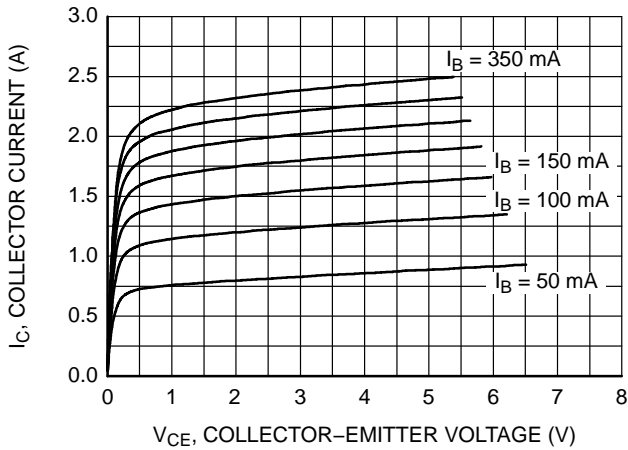


Figure 1. Static Characteristic

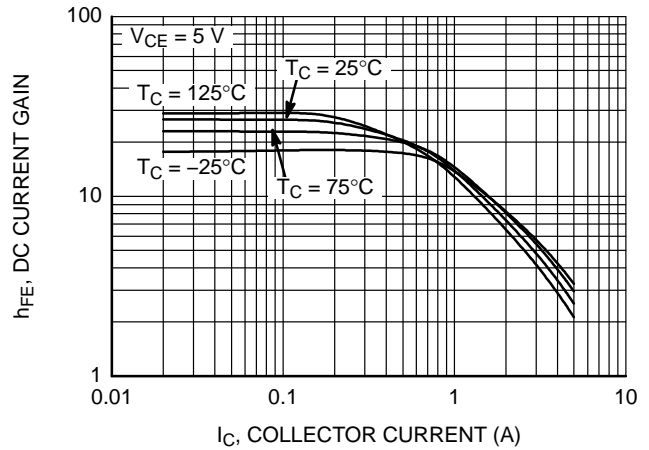


Figure 2. DC Current Gain

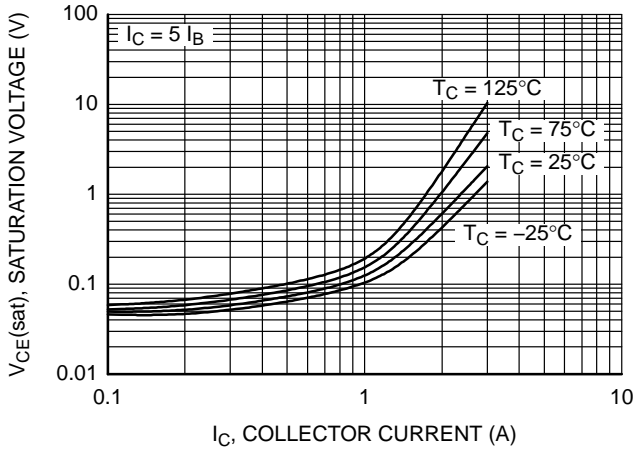


Figure 3. Saturation Voltage

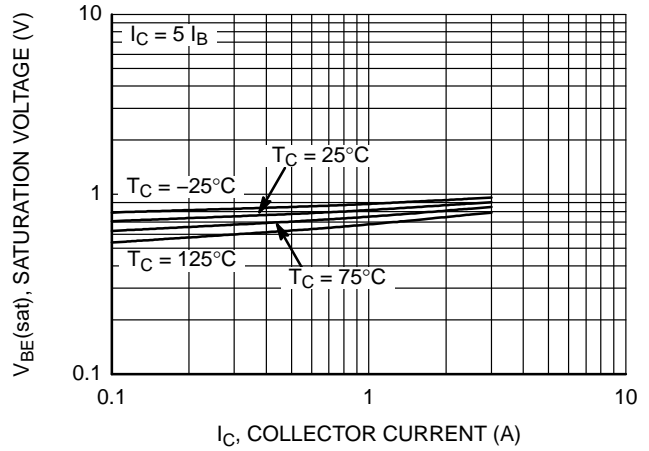


Figure 4. Saturation Voltage

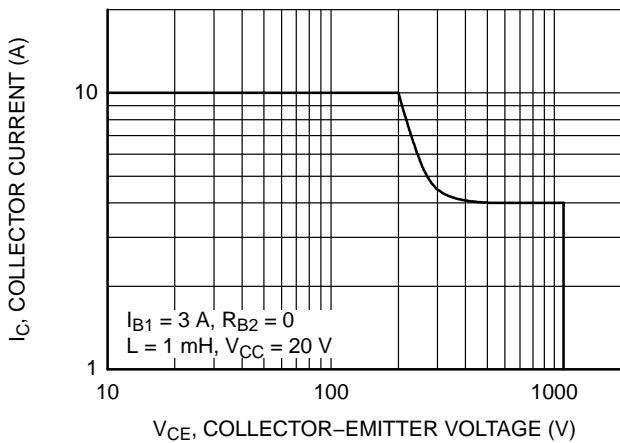


Figure 5. Reverse Bias Safe Operating Area

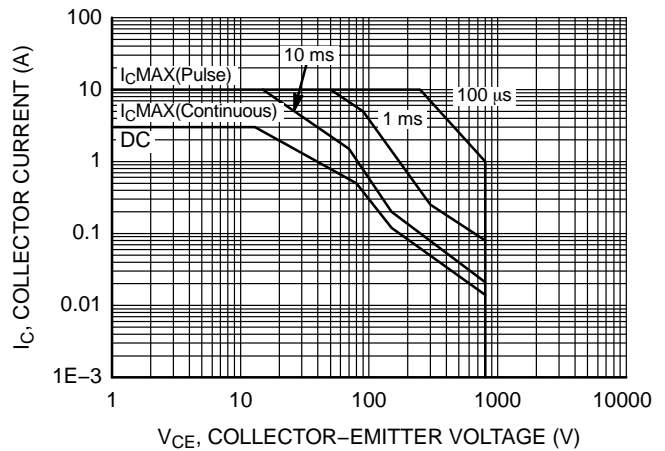


Figure 6. Forward Bias Safe Operating Area

FJPF5027

TYPICAL CHARACTERISTICS (CONTINUED)

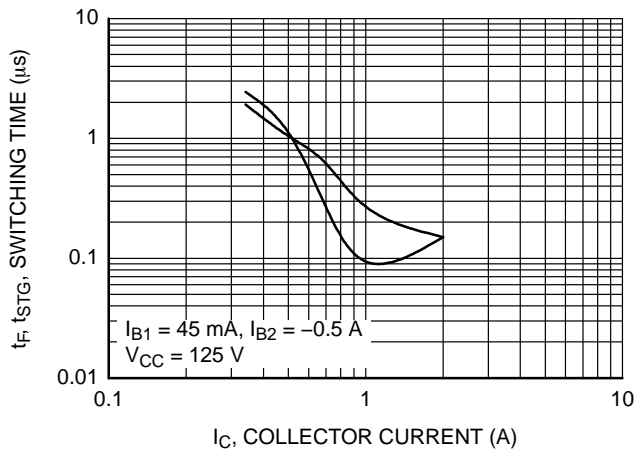


Figure 7. Resistive Load Switching Characteristics

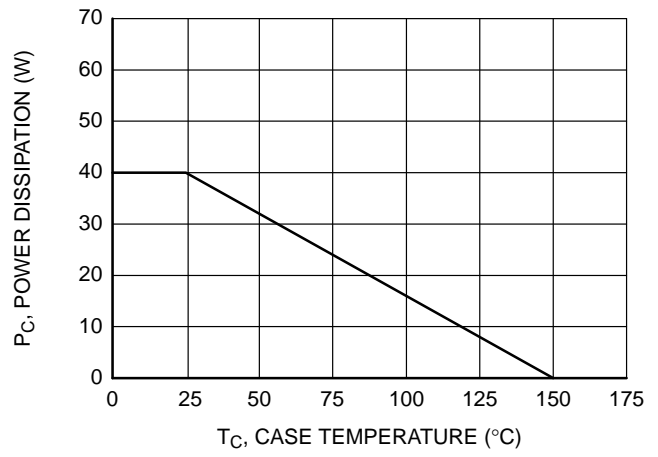


Figure 8. Power Derating

MECHANICAL CASE OUTLINE

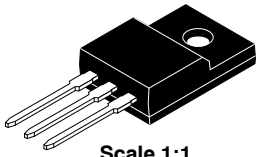
PACKAGE DIMENSIONS

ON Semiconductor®

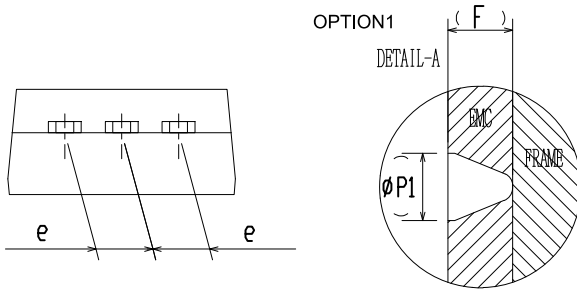
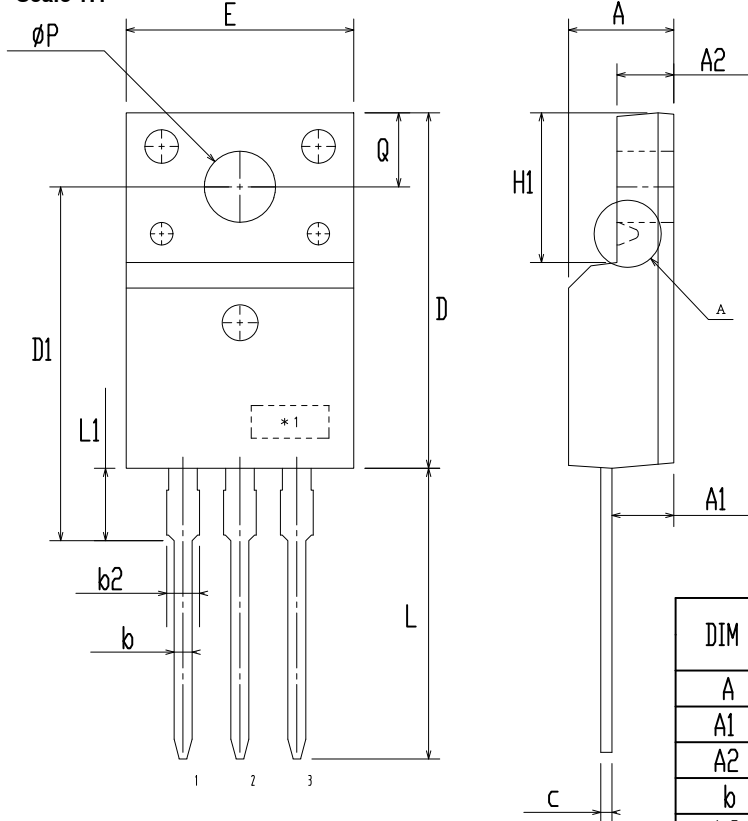


TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT ISSUE B

DATE 19 JAN 2021



Scale 1:1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
phi P	2.98	3.18	3.38
phi P1	~	1.00	~
Q	3.20	3.30	3.40

NOTES:

- A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.
- C. OPTION 1 - WITH SUPPORT PIN HOLE
OPTION 2 - NO SUPPORT PIN HOLE

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DESCRIPTION:	TO-220 FULLPACK, 3-LEAD / TO-220F-3SG	PAGE 1 OF 1

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